

TABLE 3

Dimensions	General Action		Direct Effects over I-V Characteristics of the Device					
	Increase	Decrease	V _H	V _T	Leakage	R _{on}	I _{max}	I _T
L, L _x	x		↑	≈	≈	≈	↓	≈
		x	↓	≈	≈	≈	↑	≈
Reduce below 2λ		Abrupt increment of electric field causing damages at snapbacks						
t	x		↑	↑	↑	↑	↓	↑
D1	x		↑	≈	≈	↑ Slightly	↓	↑
D2	x		≈	≈	≈	↑	↓	↑
D3		x	↑	≈	≈	↑ Slightly	↓	≈
D4	x		↑	↑	≈	≈	↑	↑
D5		x	↑	≈	≈	↑ Slightly	↓	≈
D6	x		↓	↓	≈	↓ Slightly	↓	↓
D7	x		↑	↑	≈	↑	↓	≈
D8	x		≈	≈	≈	↑	↓	≈
D9	x		↓	↓	≈	≈	↑	↓

≈: Low dependency, ↑ increase this parameter, ↓ decrease this parameter